



## 650V Super-junction Power MOSFET

### DESCRIPTION

#### 650V Super-junction Power MOSFET

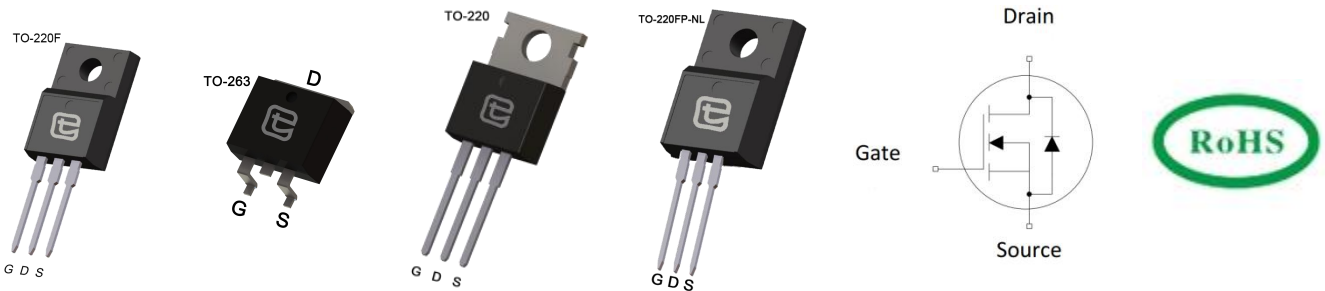
Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The Multi-EPI SJ MOSFET provide an extremely low switching, communication and conduction losses device with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler, designed by Wuxi Unigroup Microelectronics Company.

### FEATURES

- Very low FOM  $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

### APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger



### Device Marking and Package Information

Device	Package	Marking
TPA65R260M	TO-220F	65R260M
TPB65R260M	TO-263	65R260M
TPP65R260M	TO-220	65R260M
TPR65R260M	TO-220FP-NL	65R260M

### Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	0.26	$\Omega$
$I_D$	15	A
$Q_{g,typ}$	27	nC
$I_{DM}$	45	A



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted				
Parameter	Symbol	Value		Unit
		TO-220F/ TO-220FP-NL	TO-263/TO-220	
Drain-Source Voltage ( $V_{GS} = 0V$ )	$V_{DSS}$	650		V
Continuous Drain Current	$I_D$	$T_C = 25^\circ\text{C}$	15	A
		$T_C = 100^\circ\text{C}$	9	
Pulsed Drain Current (note1)	$I_{DM}$	45		A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$		V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	290		mJ
Repetitive Avalanche Energy (note2)	$E_{AR}$	0.44		mJ
Avalanche Current	$I_{AR}$	2.4		A
MOSFET dv/dt ruggedness, $V_{DS} = 0 \dots 480V$	dv/dt	50		V/ns
Power Dissipation	$P_D$	32	105	W
Continuous Body Diode Current	$I_S$	12.8		A
Pulsed Diode Forward Current (note1)	$I_{SM}$	45		
Reverse diode dv/dt (note3)	dv/dt	15		V/ns
Maximum diode commutation speed (note3)	$di_f/dt$	500		A/us
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150		$^\circ\text{C}$

Thermal Resistance				
Parameter	Symbol	Value		Unit
		TO-220F/ TO-220FP-NL	TO-263/TO-220	
Thermal Resistance, Junction-to-Case	$R_{thJC}$	3.9	1.2	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	80	62	



Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu A$
		$V_{DS} = 650V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	--	4.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 7.5A$	--	0.24	0.26	$\Omega$
Gate resistance	$R_G$	$f = 1.0\text{MHz}$ open drain	--	12.5	--	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 100V,$ $f = 1.0\text{MHz}$	--	1138	--	$\mu F$
Output Capacitance	$C_{oss}$		--	40	--	
Reverse Transfer Capacitance	$C_{rss}$		--	2.3	--	
Total Gate Charge	$Q_g$	$V_{DD} = 520V, I_D = 15A,$ $V_{GS} = 10V$	--	27	--	nC
Gate-Source Charge	$Q_{gs}$		--	5.5	--	
Gate-Drain Charge	$Q_{gd}$		--	10.5	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 15A,$ $R_G = 25\Omega$	--	25	--	ns
Turn-on Rise Time	$t_r$		--	63	--	
Turn-off Delay Time	$t_{d(off)}$		--	100	--	
Turn-off Fall Time	$t_f$		--	50	--	
<b>Drain-Source Body Diode Characteristics</b>						
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 15A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$V_R = 400V, I_F = I_S,$ $di_F/dt = 100A/\mu s$	--	410	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	4.1	--	$\mu C$
Peak Reverse Recovery Current	$I_{rrm}$		--	20	--	A

**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_{AS} = 2.4A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. Identical low side and high side switch with identical  $R_G$



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

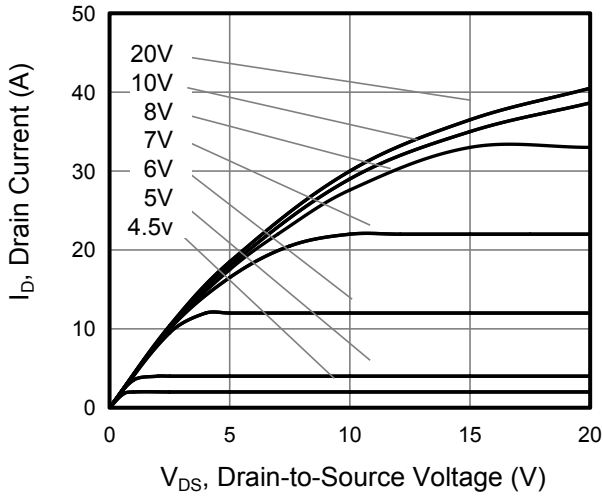


Figure 2. Transfer Characteristics

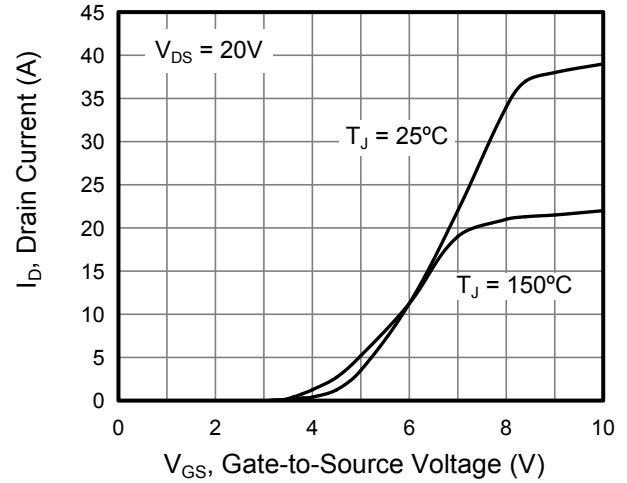


Figure 3. On-Resistance vs. Drain Current

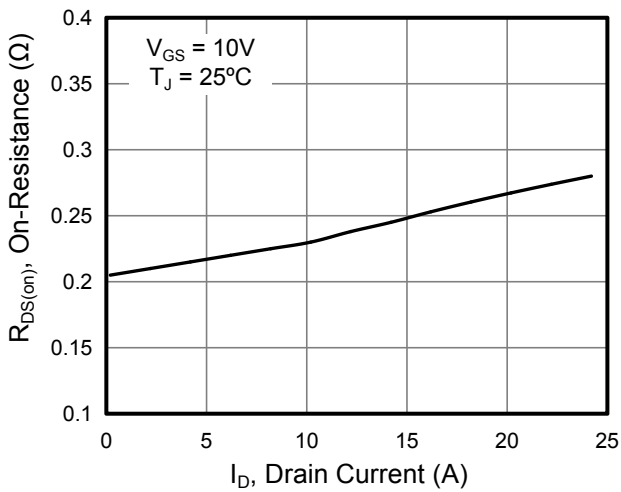


Figure 4. Capacitance

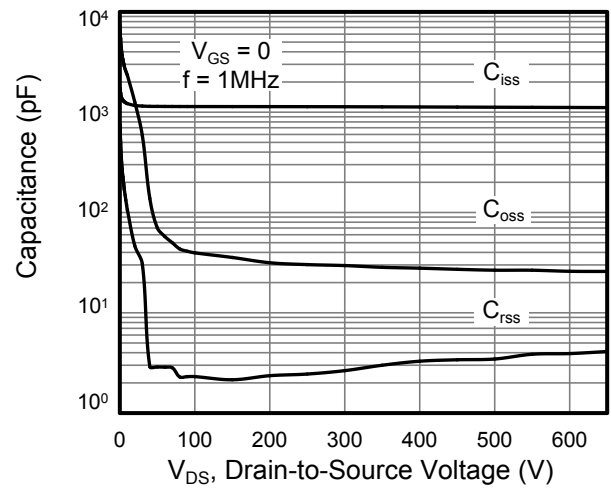


Figure 5. Gate Charge

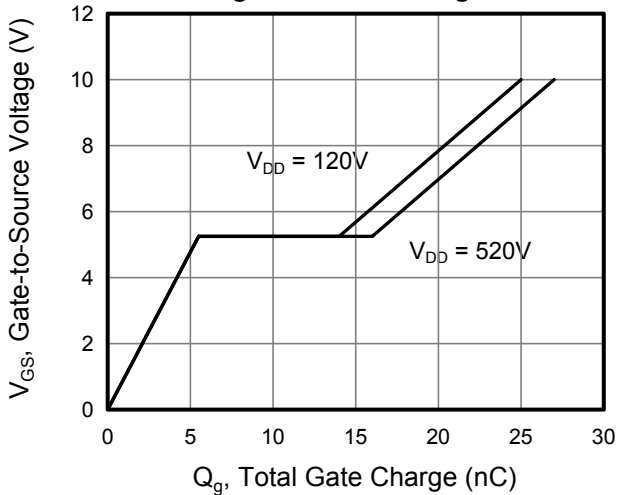
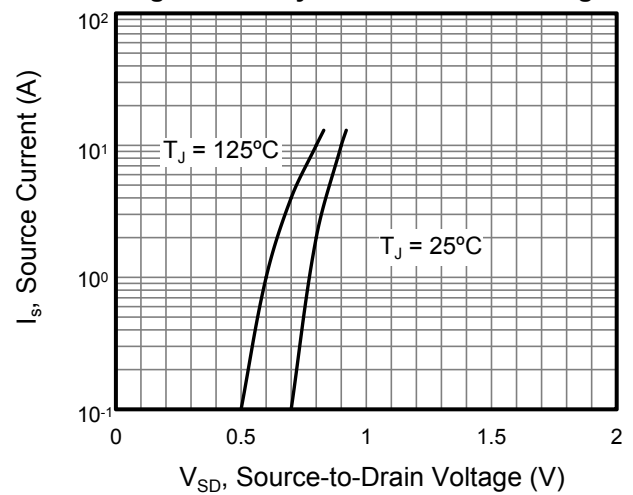


Figure 6. Body Diode Forward Voltage





Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

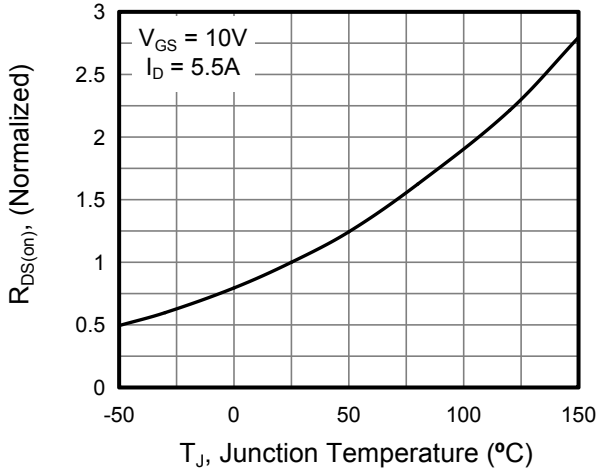


Figure 8. Breakdown voltage vs. Junction Temperature

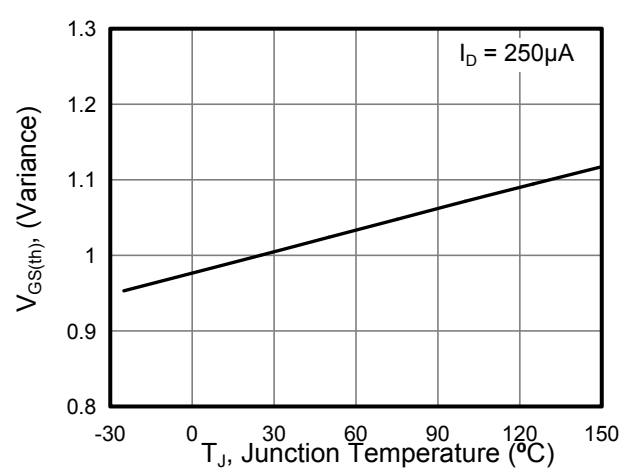


Figure 9. Transient Thermal Impedance TO-220F/TO-220FP-NL

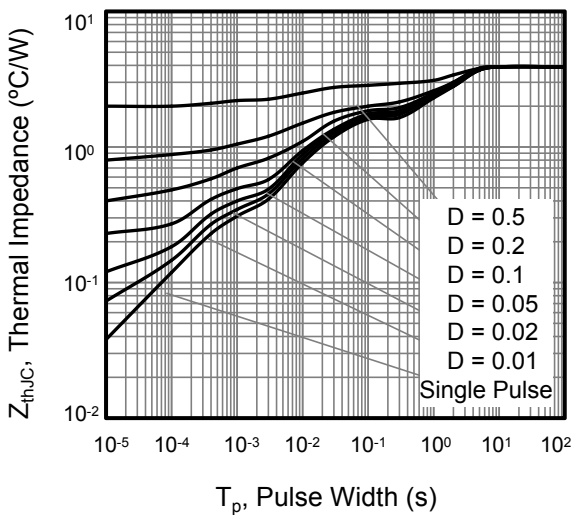


Figure 10. Safe operation area for TO-220F/TO-220FP-NL

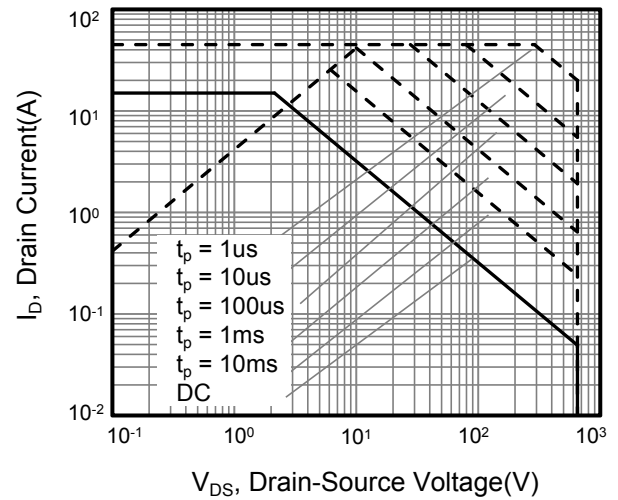


Figure 11. Transient Thermal Impedance TO-263/TO-220

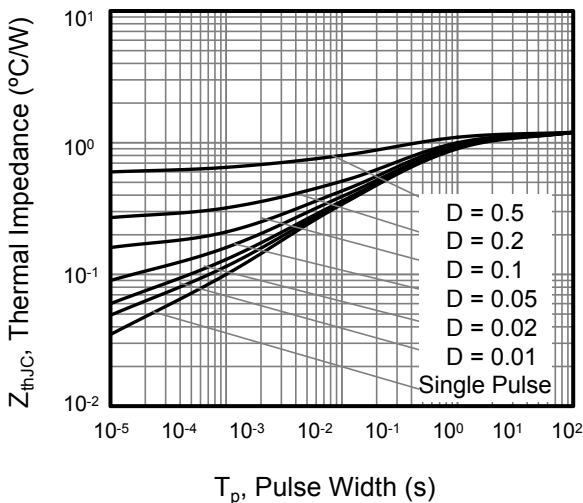


Figure 12. Safe operation area for TO-263/TO-220

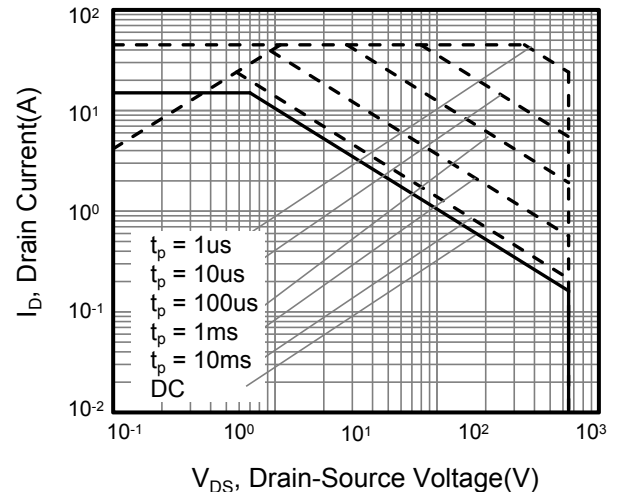




Figure A: Gate Charge Test Circuit and Waveform

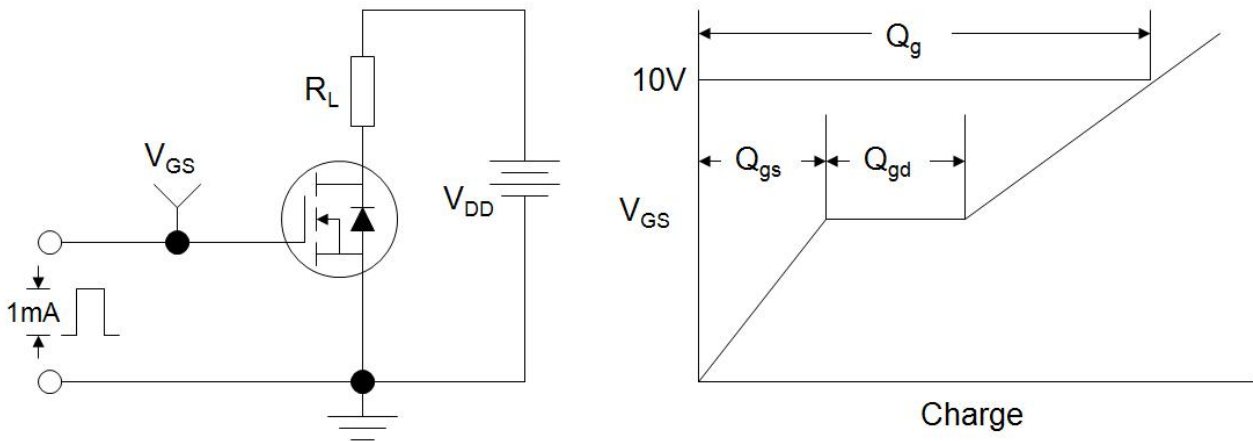


Figure B: Resistive Switching Test Circuit and Waveform

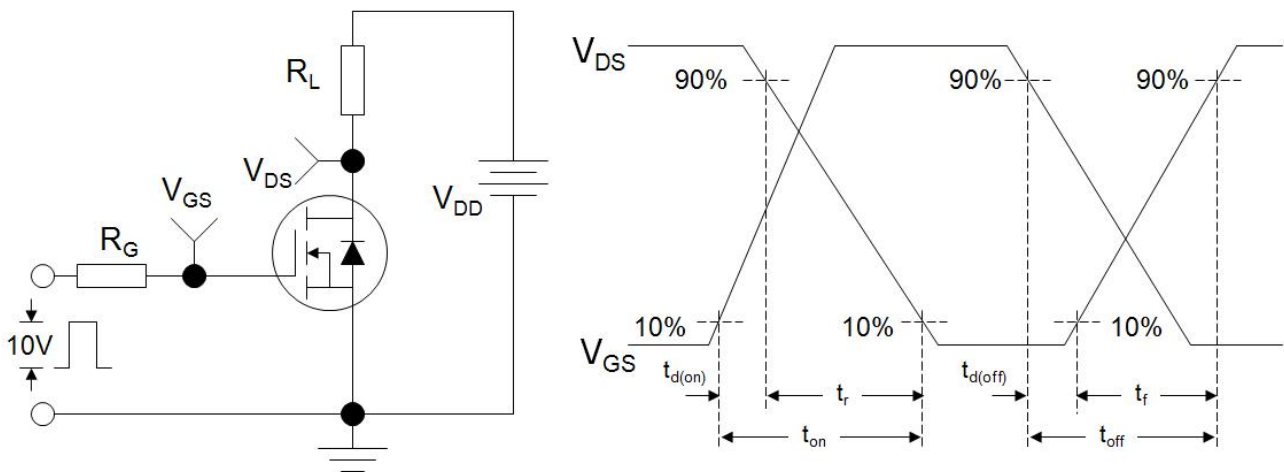
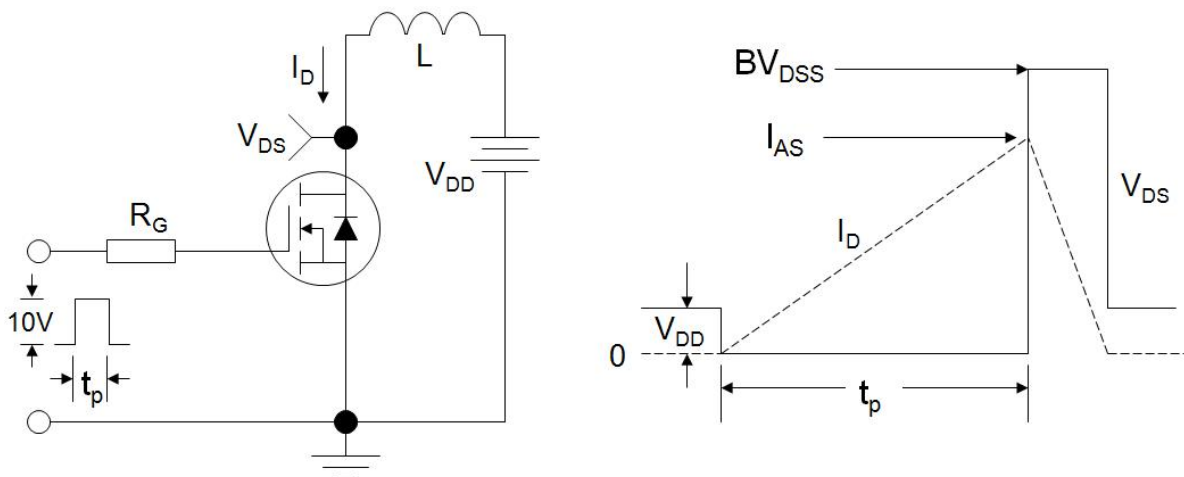
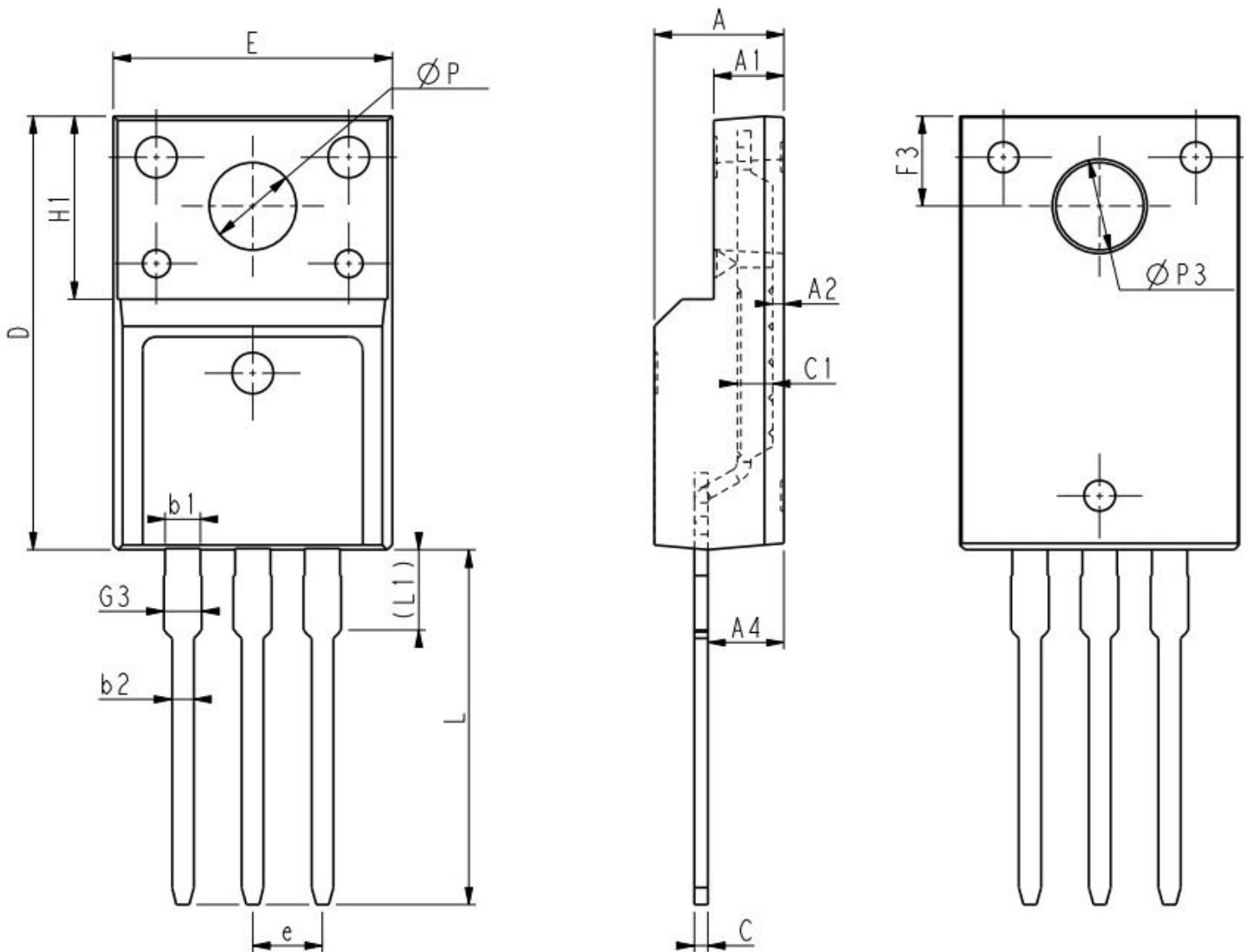


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





### TO-220F

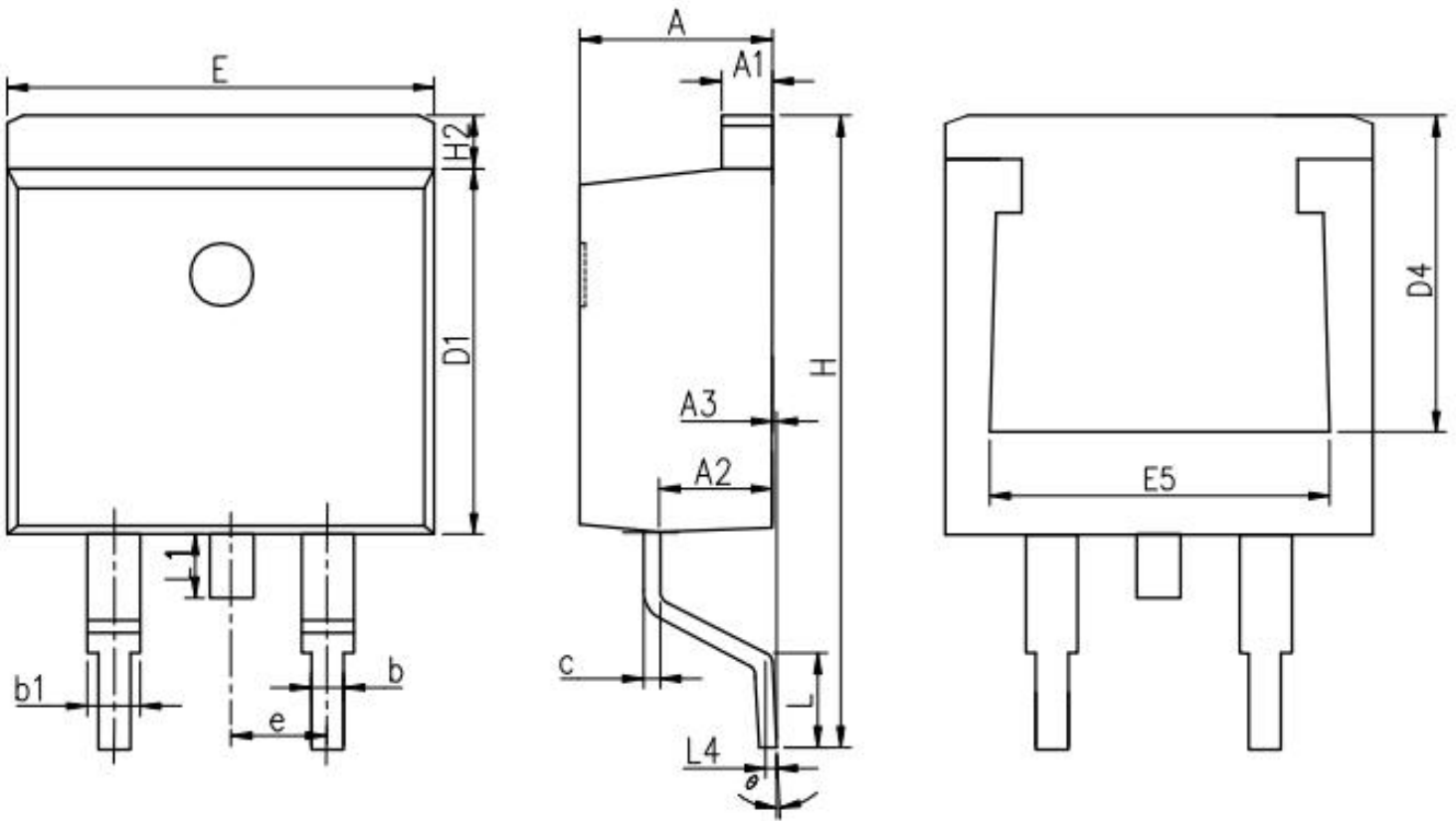


Unit:mm			
Symbol	Min.	Nom	Max.
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.30	0.45	0.60
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
c1	1.20	1.30	1.35
D	15.57	15.87	16.17
H1	6.70REF		

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.54BSC		
L	12.68	12.98	13.28
L1	2.93	3.03	3.13
$\Phi P$	3.03	3.18	3.38
$\Phi P3$	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95



### TO-263



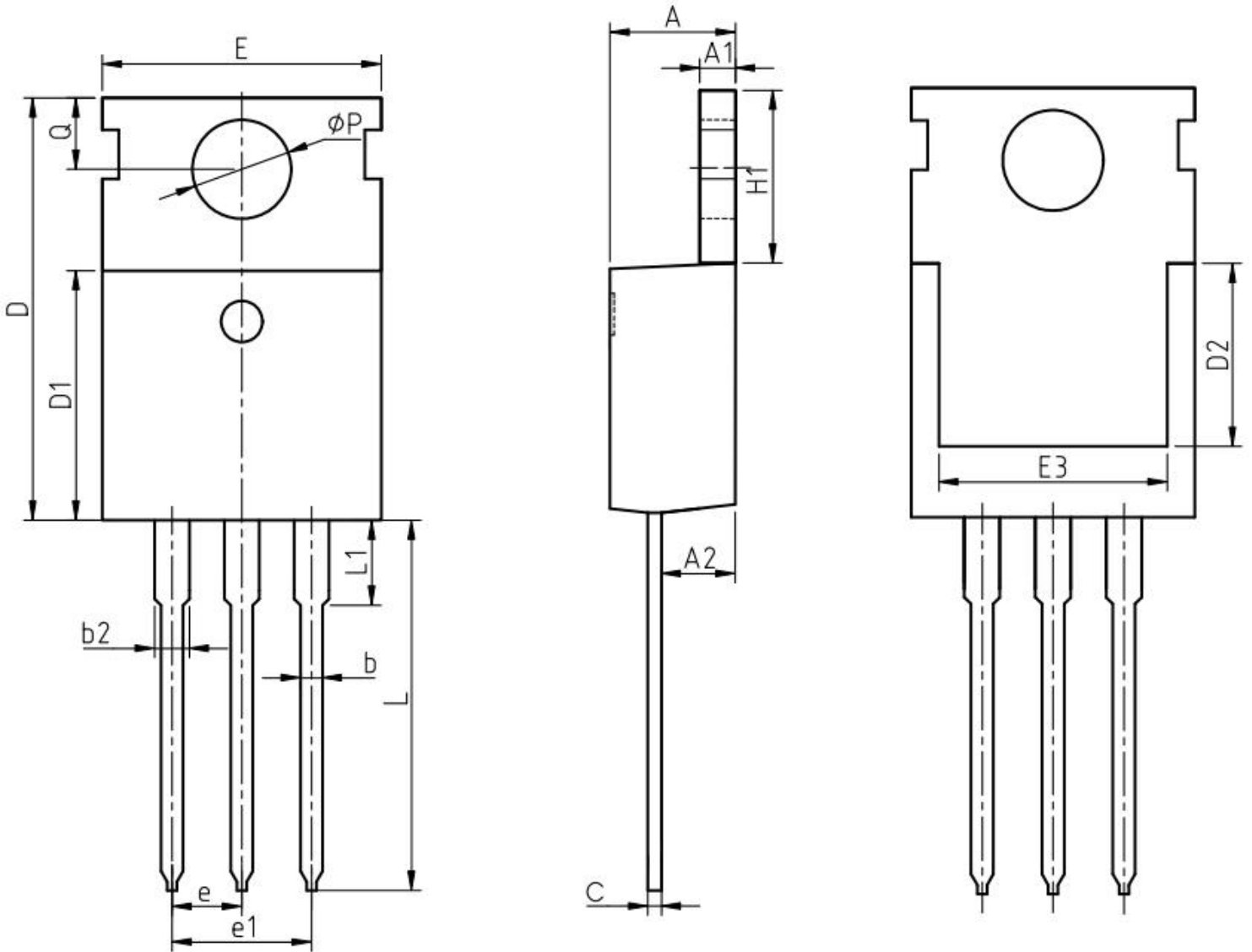
Unit:mm			
Symbol	Min.	Nom	Max.
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
A3	0.00	0.13	0.25
b	0.70	0.81	0.96
b1	1.17	1.27	1.47
c	0.30	0.38	0.53
D1	8.50	8.70	8.90
D4	6.60	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
E	9.86	10.16	10.36
E5	7.06	-	-
e	2.54BSC		
H	14.70	15.10	15.50
H2	1.07	1.27	1.47
L	2.00	2.30	2.60
L1	1.40	1.55	1.70
L4	0.25BSC		
θ	0°	5°	9°





### TO-220

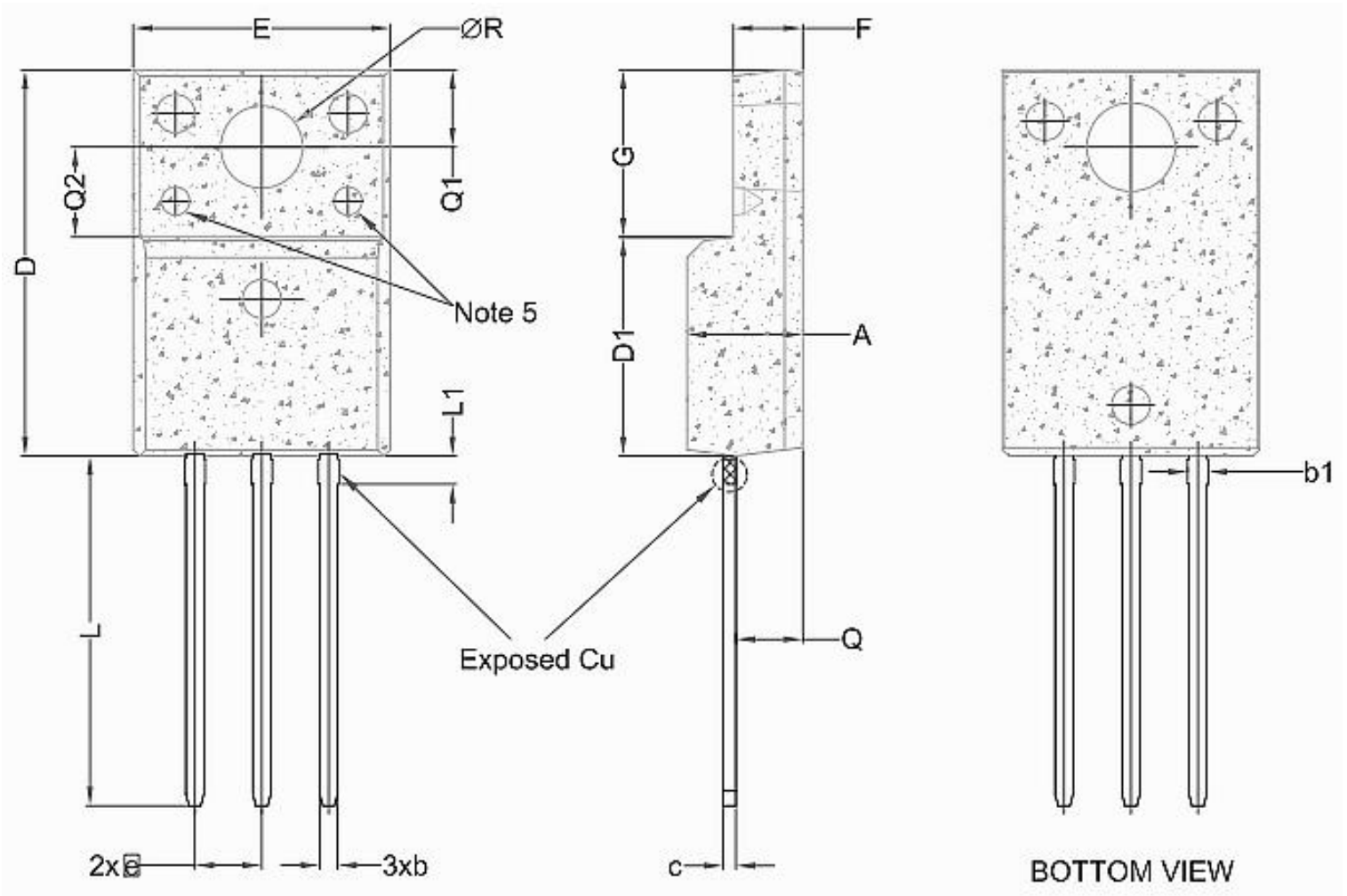


Unit:mm			
Symbol	Min.	Nom	Max.
A	4.37	4.57	4.77
A1	1.25	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.45	0.50	0.60
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
$\phi P$	3.40	3.60	3.80
Q	2.60	2.80	3.00



### TO-220FP-NL



Unit:mm				Unit:mm			
Symbol	Min.	Nom	Max.	Symbol	Min.	Nom	Max.
A	4.30	4.50	4.70	F	2.50	2.70	2.90
b	0.60	0.70	0.80	G	6.30	6.50	6.70
b1	0.60	0.80	0.90	L	13.40	13.60	13.80
c	0.45	0.50	0.60	L1	1.00	1.10	1.20
D	14.70	15.00	15.30	Q	2.50	2.60	2.70
D1	8.50 REF			Q1	2.90	3.00	3.10
e	2.60BSC			Q2	3.50 REF		
E	9.70	10.00	10.30	$\Phi R$	3.00	3.20	3.40



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